

# MOS FET MTM761100LBF

MTM761100LBF Silicon P-channel MOSFET

### For Switching

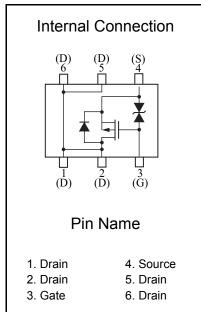
#### Features

- Low Drain-source On-state Resistance : RDS(on) typ. = 30 mΩ (VGS = -4.0 V)
- Low Drive Voltage : 1.8 V Drive
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)
- Marking Symbol : 9D

#### Packaging

Embossed type (Thermo-compression sealing) 3 000 pcs / reel (standard)

	Unit : mm					
2.0						
	0.2 0.13					
	2.1					
( <u>0. 65)(</u> 0. 1. 3	<u>0.7</u>					
1. Drain	4. Source					
2. Drain	5. Drain					
3. Gate	6. Drain					
Panasonic	WSMini6-F1-B					
JEITA	SC-113DA					
Code	—					



Absolute Maximum Ratings Ta = 25 °	С

Parameter	Symbol	Rating	Unit
Drain to Source Voltage	VDS	-12	V
Gate to Source Voltage	VGS	±8	V
Drain Current	ID	-4.0	А
Drain Current (Pulsed) <sup>*1</sup>	IDp	-16	А
Total Power Dissipation *2	PD	700	mW
Channel Temperature	Tch	150	
Operating ambient temperature	Topr	-40 to +85	°C
Storage Temperature Range	Tstg	-55 to +150	

Note: \*1 Pulse width  $\leq$  10  $\mu s, \, Duty \, cycle \leq$  1 %

\*2 Measuring on ceramic board at 40 mm  $\times$  38 mm  $\times$  0.1 mm. Absolute maximum rating PD Non-heat sink shall be made 150 mW.



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■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
Drain-source Breakdown Voltage	VDSS	ID = -1 mA, VGS = 0 V	-12			V	
Zero Gate Voltage Drain Current	IDSS	VDS = -12 V, VGS = 0 V			-1.0	μA	
Gate-source Leakage Current	IGSS	VGS = ±6.4 V, VDS = 0 V			±10	μA	
Gate-source Threshold Voltage	Vth	ID = -1.0 mA, VDS = -6.0 V	-0.3	-0.65	-1.0	V	
Drain-source On-state Resistance <sup>*1</sup>	RDS(ON)1	ID = -1 A, VGS = -4.0 V		30	42		
	RDS(ON)2	ID = -0.5 A, VGS = -2.5 V		35	55	mΩ	
	RDS(ON)3	ID = -0.2 A, VGS = -1.8 V		45	75		
Forward transfer admittance <sup>*1</sup>	Yfs	ID = -1 A, VDS = -10 V, f = 1 kHz	3.5			S	
Input Capacitance	Ciss	VDS = -10 V, VGS = 0 V		1200		pF	
Output Capacitance	Coss	f = 1 MHz		110			
Reverse Transfer Capacitance	Crss	1 - 1 10112		110			
Turn-on Time *2	ton	VDD = -6 V, VGS = 0 to -4 V ID = -1 A		30		ns	
Turn-off Time <sup>*2</sup>	toff	VDD = -6 V, VGS = -4 to 0 V ID = -1 A		300		ns	

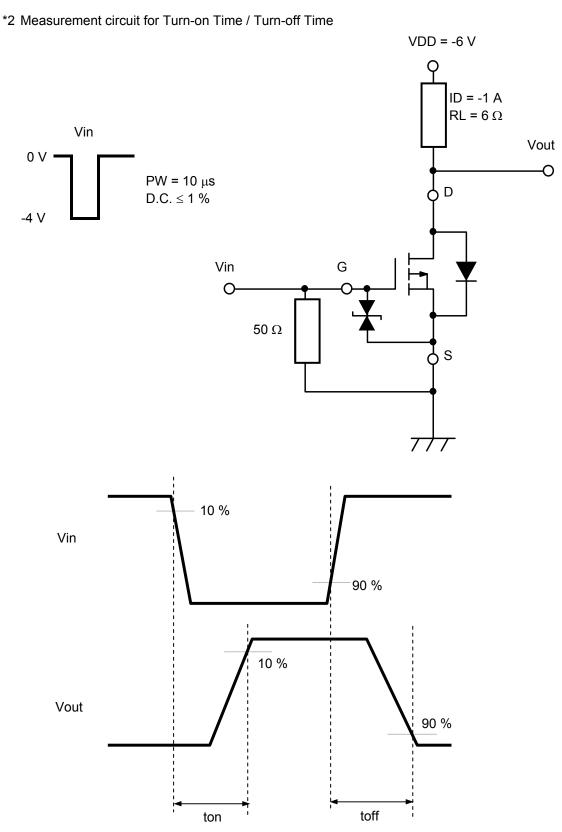
Note : Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

\*1 Pulse test : Pulse width  $\leq$  300  $\mu s, \, Duty \, cycle \leq$  2 %

\*2 Measurement circuit for Turn-on Time / Turn-off Time

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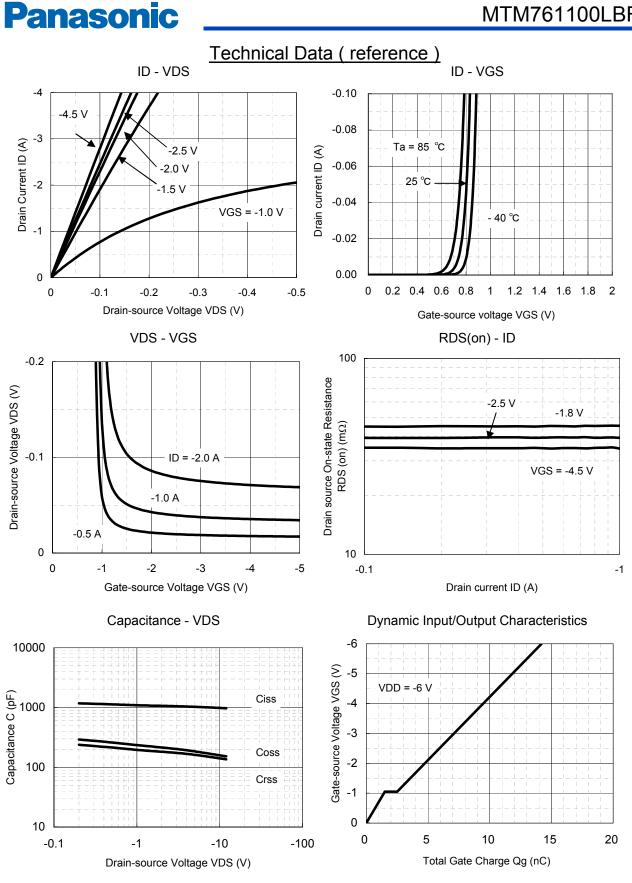




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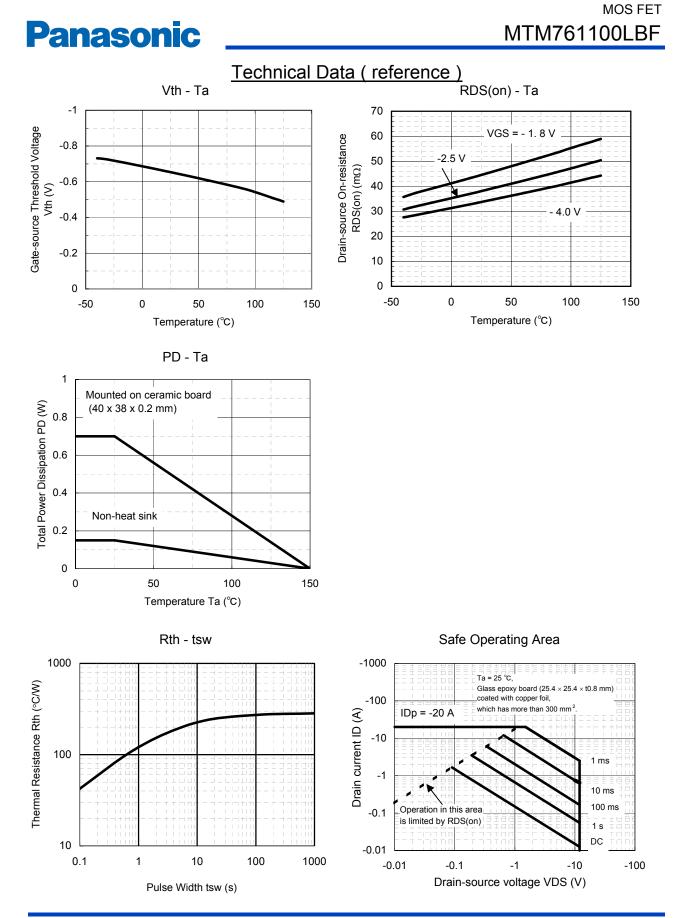
Established : 2008-01-31 Revised : 2013-10-15

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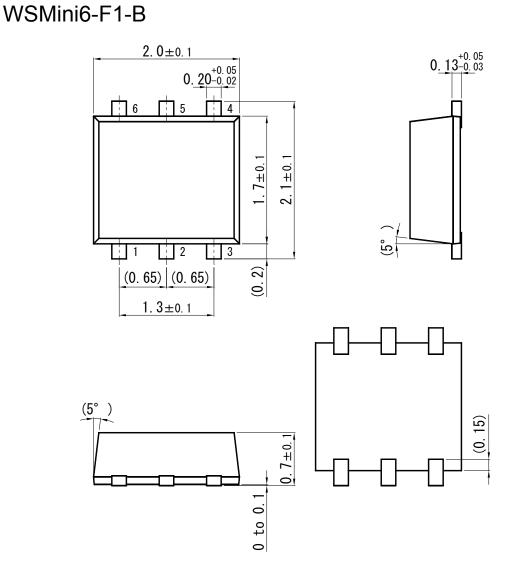


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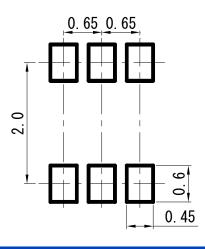


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Unit : mm



■ Land Pattern (Reference) (Unit : mm)



Established : 2008-01-31 Revised : 2013-10-15

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